

	L #	Hits	Search Text	Dbs	Time Stamp
1	L1	60746	(insulat\$4 dielectric ILD PMD oxide) near18 (voids pores porous porosity bubbles)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:39
2	L8	2713	1 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:40
3	L15	1599	1 and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:40
4	L22	3858	8 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:41
5	L29	1106	22 and spin\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:05
6	L36	176683	(heat\$3 thermal thermally evaporat\$4 vaopris\$4 vaporis\$4) same (voids pores porous porosity bubbles)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:45
7	L43	1517	22 and 36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:44
8	L50	471	43 and spin\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:05
9	L57	101801	(heat\$3 thermal thermally evaporat\$4 vaopris\$4 vaporis\$4) near25 (voids pores porous porosity bubbles)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:08
10	L64	103226	(heat\$3 thermal thermally evaporat\$4 vaporiz\$4 vaporis\$4) near25 (voids pores porous porosity bubbles)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:59
11	L106	884	22 and 64	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:11
12	L113	259	106 and spin\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:47
13	L120	59	113 and @rlad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:11
14	L127	121	113 and @ad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:12
15	L134	137	120 127	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:47
16	L141	3622	(heat\$3 thermal thermally evaporat\$4 vaporis\$4,vaporiz\$4) near25 ((voids pores porous porosity bubbles) near5 (expand\$ expansion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:11
17	L148	61	22 and 141	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:11
18	L155	11	148 and @rlad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:11
19	L162	24	148 and @ad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:12
20	L169	29	155 162	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:16
21	L176	11511	(photoresist resist) near3 (siloxane si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:06
22	L183	3	(photoresist resist) near3 (includ\$3 incorporat\$3 consist\$3 compris\$3) near3 (siloxane si silicon) near3 (carbon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:09